

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Tsuneco INABA

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

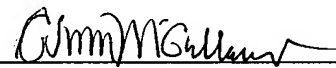
- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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DOCKET NO: 244989US2S

Sheet 1 of 1

IN RE APPLICATION OF: Tsuneo INABA

SERIAL NO: New Application

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FOR: MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE

STATEMENT OF RELEVANCY

Reference AO (JP 2002-25245) on Form PTO- 1449:

This document claims that 2 resistive elements are connected each other, the each elements store the opposite data, a mode between the elements is connected to source sink, and the data is detected by the measuring each resistance of the elements.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

244989US2S

SERIAL NO.

New Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Tsuneo INABA

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,946,227	08/31/99	Peter K. NAJI			
	AB	5,986,925	11/16/99	Peter K. NAJI, et al.			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	2002-25245	01/25/02	Japan		x
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AV	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2000, 8 Pages				
	AW	M. DURLAM, et al., "NONVOLATILE RAM BASED ON MAGNETIC TUNNEL JUNCTION ELEMENTS", IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2000, 7 Pages				
	AX	Peter K. NAJI, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2001, 9 Pages				
	AY	Kouichi YAMADA, et al., "A Novel Sensing Scheme for a MRAM with a 5% MR Ratio", SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, Session C12-1, June 2001, 2 Pages				
	AZ					<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.